

## Electronic Acknowledgement Receipt

<b>EFS ID:</b>	9687751
<b>Application Number:</b>	10577175
<b>International Application Number:</b>	
<b>Confirmation Number:</b>	3451
<b>Title of Invention:</b>	Method for Self-Supported Transfer of a Fine Layer by Pulsation after Implantation or Co-Implantation
<b>First Named Inventor/Applicant Name:</b>	Nguyet-Phuong Nguyen
<b>Customer Number:</b>	90678
<b>Filer:</b>	Jasper W. Dockrey/Nkosi Harvey
<b>Filer Authorized By:</b>	Jasper W. Dockrey
<b>Attorney Docket Number:</b>	9905/40 (BIF116533US/)
<b>Receipt Date:</b>	18-MAR-2011
<b>Filing Date:</b>	03-APR-2007
<b>Time Stamp:</b>	16:14:24
<b>Application Type:</b>	U.S. National Stage under 35 USC 371

### Payment information:

Submitted with Payment	no
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### File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	NPL Documents	Eaglesham_et_al.pdf	272298 5602f2e891fcd72813254578fcd7de7e3d22897b	no	4

### Warnings:

### Information:

2	NPL Documents	EerNisse_1973.pdf	768866	no	8
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<b>Total Files Size (in bytes):</b>			31408215		

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**New Applications Under 35 U.S.C. 111**

**If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.**

**National Stage of an International Application under 35 U.S.C. 371**

**If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.**

**New International Application Filed with the USPTO as a Receiving Office**

**If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.**